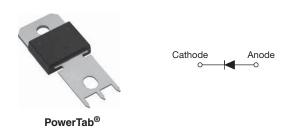
VS-80EBU04

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Vishay Semiconductors

Ultrafast Soft Recovery Diode, 80 A FRED Pt®



| PRODUCT SUMMARY | | | | | |
|----------------------------------|-----------------------|--|--|--|--|
| Package | PowerTab [®] | | | | |
| I _{F(AV)} | 80 A | | | | |
| V _R | 400 V | | | | |
| V _F at I _F | 1.3 V | | | | |
| t _{rr} (typ.) | See recovery table | | | | |
| T _J max. | 175 °C | | | | |
| Diode variation | Single die | | | | |

FEATURES

- Ultrafast recovery time
- 175 °C max. operating junction temperature
- Screw mounting only
- Designed and qualified according to JEDEC-JESD47
- PowerTab[®] package
- Material categorization: For definitions of compliance please see <u>www.vishay.com/doc?99912</u>

BENEFITS

- Reduced RFI and EMI
- Higher frequency operation
- Reduced snubbing
- Reduced parts count

DESCRIPTION/APPLICATIONS

These diodes are optimized to reduce losses and EMI/RFI in high frequency power conditioning systems.

The softness of the recovery eliminates the need for a snubber in most applications. These devices are ideally suited for HF welding, power converters and other applications where switching losses are not significant portion of the total losses.

| ABSOLUTE MAXIMUM RATINGS | | | | | |
|--|-----------------------------------|--------------------------|-------------|-------|--|
| PARAMETER | SYMBOL | TEST CONDITIONS | MAX. | UNITS | |
| Cathode to anode voltage | V _R | | 400 | V | |
| Continuous forward current | I _{F(AV)} | T _C = 101 °C | 80 | | |
| Single pulse forward current | I _{FSM} | $T_{C} = 25 \ ^{\circ}C$ | 800 | А | |
| Maximum repetitive forward current | I _{FRM} | Square wave, 20 kHz | 160 | | |
| Operating junction and storage temperatures | T _J , T _{Stg} | | - 55 to 175 | °C | |

| ELECTRICAL SPECIFICATIONS (T _J = 25 °C unless otherwise specified) | | | | | | | |
|--|-------------------------------------|--|---|------|------|-------|--|
| PARAMETER | SYMBOL | TEST CONDITIONS MIN. | | TYP. | MAX. | UNITS | |
| Breakdown voltage, blocking voltage | V _{BR} , V _r | I _R = 100 μA | | - | - | | |
| | | I _F = 80 A | - | 1.1 | 1.3 | v | |
| Forward voltage | V _F | I _F = 80 A, T _J = 175 °C | - | 0.92 | 1.08 | | |
| | | I _F = 80 A, T _J = 125 °C | | 0.98 | 1.15 | | |
| Reverse leakage current I _R | | $V_{R} = V_{R}$ rated | - | - | 50 | μA | |
| | | $T_J = 150 \text{ °C}, V_R = V_R \text{ rated}$ | - | - | 2 | mA | |
| Junction capacitance | CT | V _R = 200 V - 50 - | | pF | | | |
| Series inductance | L _S | Measured lead to lead 5 mm from package body - 3.5 - n | | nH | | | |

Revision: 11-Dec-12

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Document Number: 93025

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COMPLIANT

VS-80EBU04



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| DYNAMIC RECOVERY CHARACTERISTICS ($T_J = 25$ °C unless otherwise specified) | | | | | | | |
|---|------------------|---|---|------|------|-------|-----------|
| PARAMETER | SYMBOL | TEST CON | MIN. | TYP. | MAX. | UNITS | |
| | | $I_F = 1 \text{ A}, \text{ d}I_F/\text{d}t = 200 \text{ A}/\mu\text{s}, \text{ V}_R = 30 \text{ V}$ | | - | 50 | 60 | |
| Reverse recovery time t _{rr} | t _{rr} | T _J = 25 °C | | - | 87 | - | ns - A |
| | | T _J = 125 °C | | - | 151 | - | |
| Peak recovery current | I _{RRM} | T _J = 25 °C | I _F = 80 A V _R = 200 V dI _F /dt = 200 A/μs | - | 9.3 | - | |
| | | T _J = 125 °C | | - | 17.2 | - | |
| Reverse recovery charge | Q _{rr} | T _J = 25 °C | | - | 405 | - | nC |
| | | T _J = 125 °C | | - | 1300 | - | nc |

| THERMAL - MECHANICAL SPECIFICATIONS | | | | | | |
|---|-------------------|--|-------------|------|-------------|---------------------|
| PARAMETER | SYMBOL | TEST CONDITIONS MIN. TYP. MAX | | MAX. | UNITS | |
| Thermal resistance, junction to case | R _{thJC} | | - | - | 0.70 | °C/W |
| Thermal resistance, junction to heatsink | R _{thCS} | Mounting surface, flat, smooth and greased | - | 0.2 | - | 0/00 |
| Weight | | | - | - | 5.02 | g |
| weight | | | - | 0.18 | - | oz. |
| Mounting torque | | | 1.2 (10) | - | 2.4 (20) | N · m (lbf · in) |
| Marking device | | Case style PowerTab [®] | | 80EE | BU04 | |



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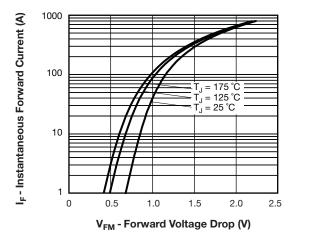


Fig. 1 - Maximum Forward Voltage Drop Characteristics

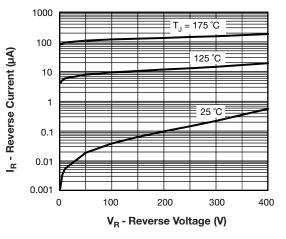
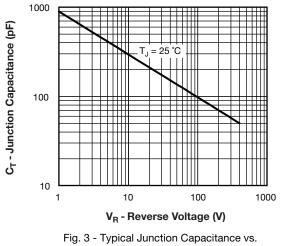
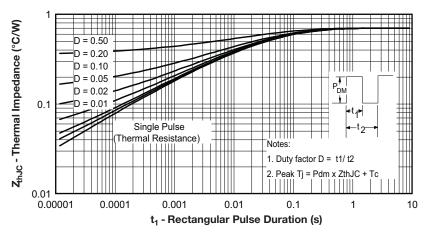
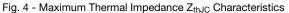


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage



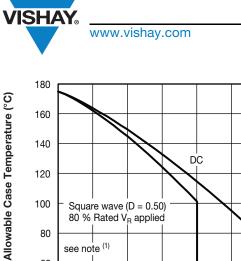
g. 3 - Typical Junction Capacitance vs Reverse Voltage

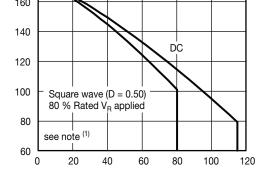




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IF(AV) - Average Forward Current (A)

Fig. 5 - Maximum Allowable Case Temperature vs. Average Forward Current

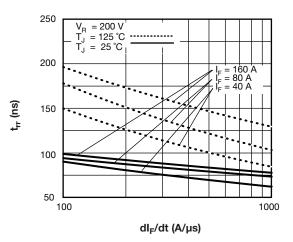


Fig. 7 - Typical Reverse Recovery Time vs. dl_F/dt

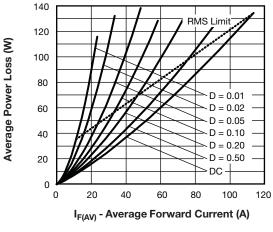


Fig. 6 - Forward Power Loss Characteristics

Note

(1) Formula used: $T_C = T_J - (Pd + Pd_{REV}) \times R_{thJC}$;

 $\begin{array}{l} \mathsf{Pd} = \mathsf{Forward} \ \mathsf{power} \ \mathsf{loss} = \mathsf{I}_{\mathsf{F}(\mathsf{AV})} \times \mathsf{V}_{\mathsf{FM}} \ \mathsf{at} \ (\mathsf{I}_{\mathsf{F}(\mathsf{AV})}/\mathsf{D}) \ (\mathsf{see} \ \mathsf{fig.} \ \mathsf{6}); \\ \mathsf{Pd}_{\mathsf{REV}} = \mathsf{Inverse} \ \mathsf{power} \ \mathsf{loss} = \mathsf{V}_{\mathsf{R1}} \times \mathsf{I}_{\mathsf{R}} \ (\mathsf{1} - \mathsf{D}); \ \mathsf{I}_{\mathsf{R}} \ \mathsf{at} \ \mathsf{V}_{\mathsf{R1}} = \mathsf{80} \ \% \ \mathsf{rated} \ \mathsf{V}_{\mathsf{R}} \end{array}$

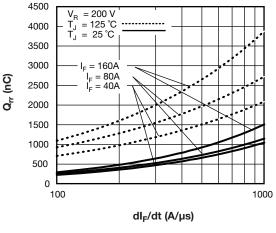


Fig. 8 - Typical Stored Charge vs. dl_F/dt

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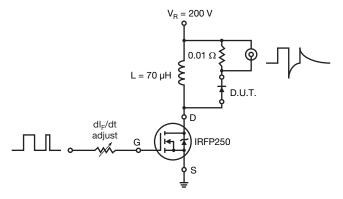
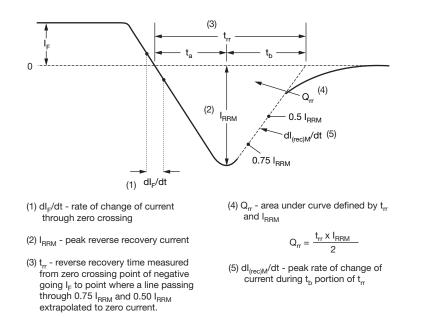
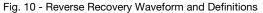


Fig. 9 - Reverse Recovery Parameter Test Circuit







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ORDERING INFORMATION TABLE

| Device code | VS- | 80 | Е | в | U | 04 | |
|-------------|-----|------|------------|----------------------|-----------|----------|-------|
| | 1 | 2 | 3 | 4 | 5 | 6 | |
| | 1 - | Visł | nay Sem | iconduc | tors pro | duct | |
| | 2 - | Cur | rent ratii | ng (80 = | 80 A) | | |
| | 3 - | E = | Single o | liode | | | |
| | 4 - | В= | PowerT | ab [®] (ult | rafast/hy | yperfast | only) |
| | 5 - | U = | Ultrafas | t recove | ery | | |
| | 6 - | Volt | age rati | ng (04 = | 400 V) | | |

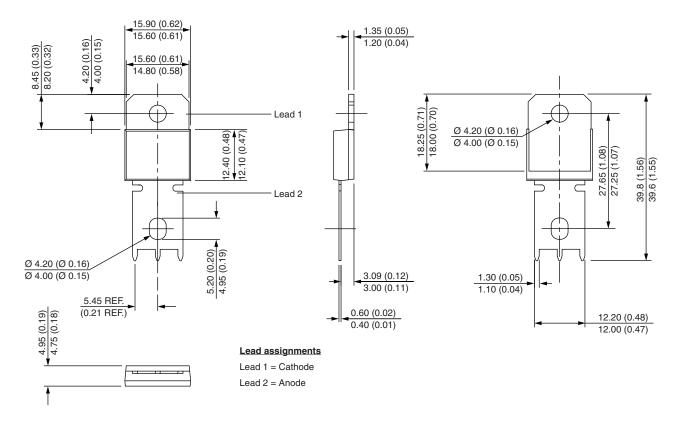
| LINKS TO RELATED DOCUMENTS | | | | | |
|-------------------------------------|--------------------------|--|--|--|--|
| Dimensions www.vishay.com/doc?95240 | | | | | |
| Part marking information | www.vishay.com/doc?95370 | | | | |
| Application note | www.vishay.com/doc?95179 | | | | |



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PowerTab[®]

DIMENSIONS in millimeters (inches)





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